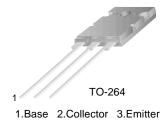


## KSC5200

### **Audio Power Amplifier**

- High Current Capability : I<sub>C</sub>=13A
- High Power Dissipation
- Wide S.O.A
- Complement to KSA1943



## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	230	V
V <sub>CEO</sub>	Collector-Emitter Voltage	230	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current(DC)	13	Α
I <sub>B</sub>	Base Current	1.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	130	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 50 ~ 150	°C

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=5mA$ , $I_E=0$	230			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞	230			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=5mA$ , $I_C=0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =230V, $I_{E}$ =0			5.0	uA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_C$ =0			5.0	uA
h <sub>FE1</sub>	* DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1A	55		160	
h <sub>FE2</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =7A	35	60		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =8A, I <sub>B</sub> =0.8A		0.4	3.0	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =7A		1.0	1.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =1A		30		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz		200		pF
* Pulse Test : PW=2	0us	•	•	•	•	•

## **h**<sub>FE</sub> Classification

Classification	R	0
h <sub>FE1</sub>	55 ~ 110	80 ~ 160

# **Typical Characteristics**

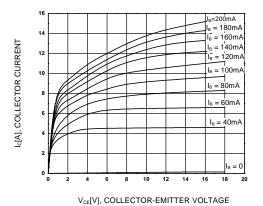


Figure 1. Static Characteristic

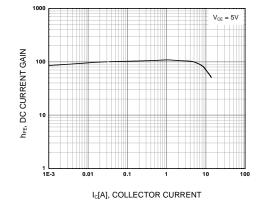


Figure 2. DC current Gain

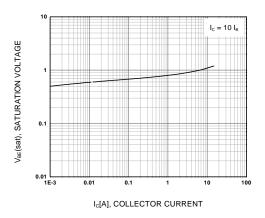


Figure 3. Base-Emitter Saturation Voltage

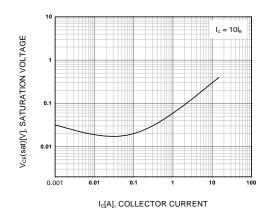


Figure 4. Collector-Emitter Saturation Voltage

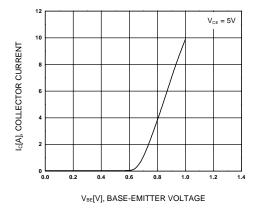
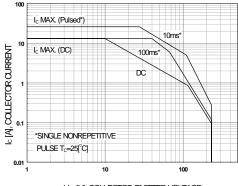


Figure 5. Base-Emitter On Voltage



 $V_{CE}\left[V\right]\!,COLLECTOR\text{-}EMITTER\,VOLTAGE$ 

Figure 6. Safe Operating Area

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# **Typical Characteristics**

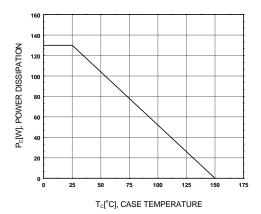
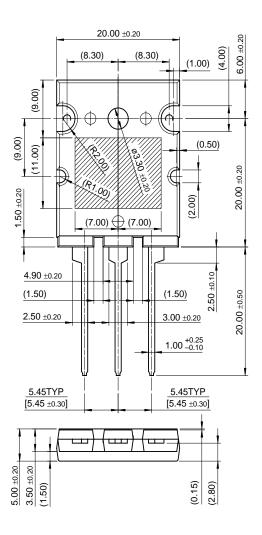
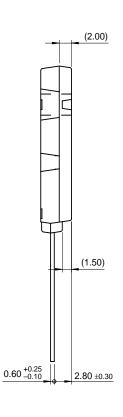


Figure 7. Power Derating

## **Package Demensions**

## TO-264





Dimensions in Millimeters

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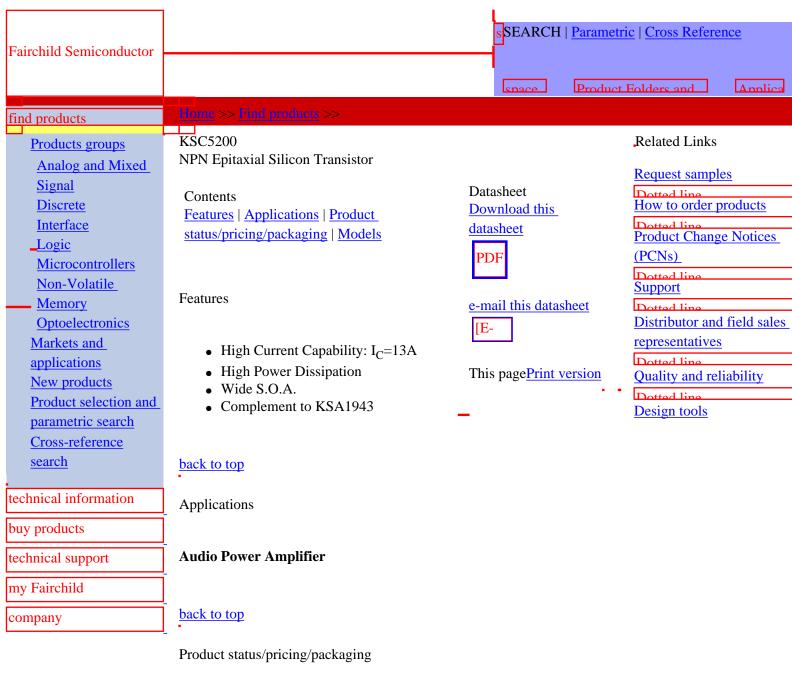
Rev. H4

### **PRODUCT STATUS DEFINITIONS**

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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Product status		Pricing*	Package type	Leads	Packing method
KSC5200OTU	Full Production	\$1.79	<u>TO-264</u>	3	RAIL
KSC5200RTU	Full Production	\$1.79	<u>TO-264</u>	3	RAIL

<sup>\* 1,000</sup> piece Budgetary Pricing

### back to top

### Models

Package & leads Condition		Temperature range   Software version		Revision date	
PSPICE					
TO-264-3	Electrical/Thermal	-25°C to 100°C	9	Mar 17, 2000	

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